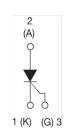


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# Thyristor High Voltage, Phase Control SCR, 30 A





PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub> 20 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V					
V <sub>TM</sub>	1.3 V					
I <sub>GT</sub>	45 mA					
T <sub>J</sub>	-40 °C to +125 °C					
Package	TO-247AC 3L					
Circuit configuration	Single SCR					

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

### **DESCRIPTION**

The VS-30TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	20	^			
I <sub>RMS</sub>		30	Α Α			
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V			
I <sub>TSM</sub>		300	A			
V <sub>T</sub>	20 A, T <sub>J</sub> = 25 °C	1.3	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T <sub>J</sub>		-40 to +125	°C			

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-30TPS08-M3	800	900	10				
VS-30TPS12-M3	1200	1300	10				



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ABSOLUTE MAXIMUM RATING	S				
PARAMETER	SYMBOL	TEST COM	NDITIONS	VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 95 °C, 180° conduction	half sine wave	20	
Maximum RMS on-state current	I <sub>RMS</sub>			30	٨
Maximum peak, one-cycle		10 ms sine pulse, rated V <sub>RRM</sub>	applied	250	Α
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage	reapplied	300	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub>	applied	310	A2-
	1-1	10 ms sine pulse, no voltage reapplied		442	- A <sup>2</sup> s
Maximum I²√t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied		4420	A²√s
Maximum on-state voltage drop	V <sub>TM</sub>	20 A, T <sub>J</sub> = 25 °C		1.3	V
On-state slope resistance	r <sub>t</sub>	T 405.00		12	mΩ
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.0	V
Maximum reverse and direct leakage	1 /1	T <sub>J</sub> = 25 °C	\/t \/ \/ \/	0.5	
current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	10	Л
Maximum holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $T_J = 25$ °C		150	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		200	
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum, linear to 80 % V <sub>DRM</sub> , R <sub>g</sub> -k = open		500	V/µs
Maximum rate of rise of turned-on current	dl/dt	-		150	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	w	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	_ vv	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45		
1.950		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -10 °C	2.5		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	\ \	
Maximum DC gate voltage not to trigger V <sub>GD</sub>					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value		mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9			
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs		
Typical turn-off time	tq	1J = 125 C	110			



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and st temperature range	orage	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	- DC operation	0.8		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>	DC operation	40	°C/W	
Maximum thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2		
Approximate weight				6	g	
Approximate weight				0.21	oz.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	(lbf · in)	
Marking device			Consistua TO 247AC 21	30TPS08		
			Case style TO-247AC 3L	30TPS12		

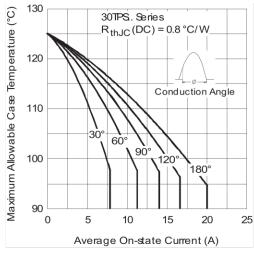


Fig. 1 - Current Rating Characteristics

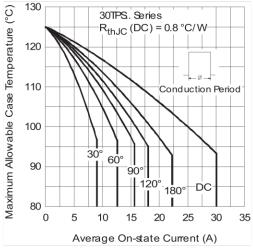


Fig. 2 - Current Rating Characteristics

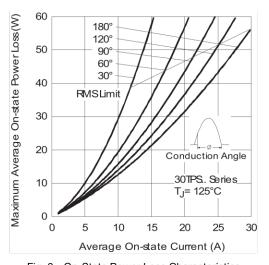


Fig. 3 - On-State Power Loss Characteristics

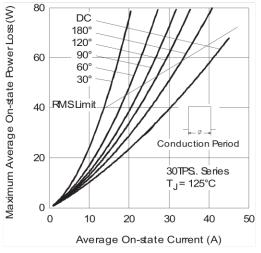


Fig. 4 - On-State Power Loss Characteristics

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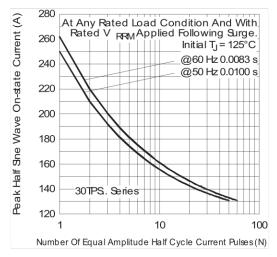


Fig. 5 - Maximum Non-Repetitive Surge Current

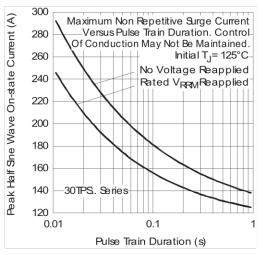


Fig. 6 - Maximum Non-Repetitive Surge Current

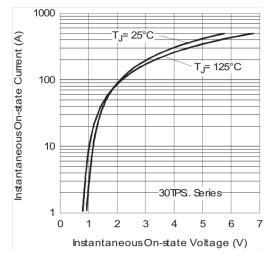


Fig. 7 - On-State Voltage Drop Characteristics

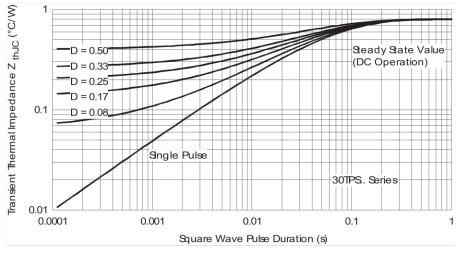


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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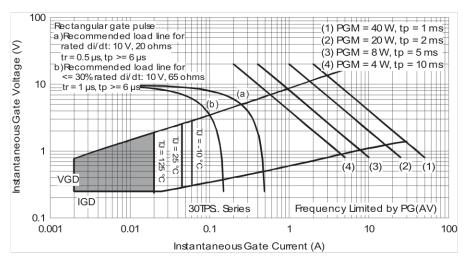
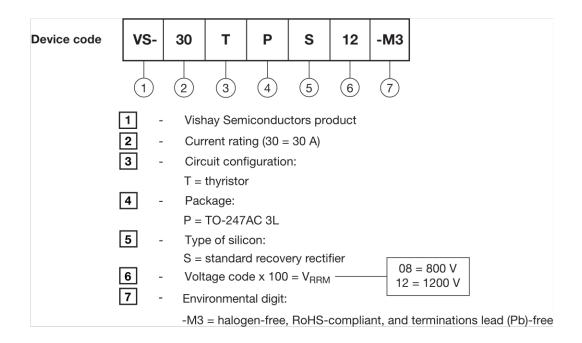


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-30TPS08-M3	25	500	Antistatic plastic tubes			
VS-30TPS12-M3	25	500	Antistatic plastic tubes			

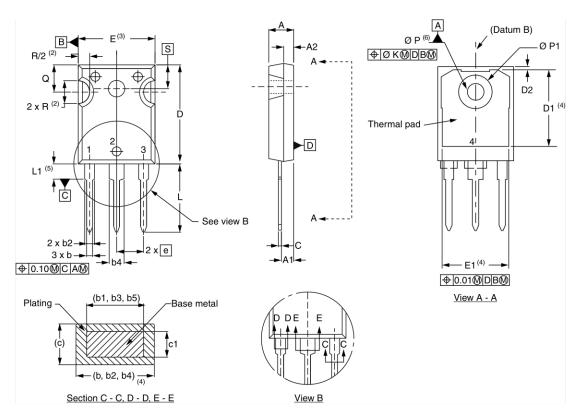
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96138</u>				
Part marking information	www.vishay.com/doc?95007			



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### **TO-247AC 3L**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D2	0.51	1.35	0.020	0.053		
E	15.29	15.87	0.602	0.625	3	
E1	13.46	-	0.53	-		
е	5.46	BSC	0.215	BSC		
ØK	0.2	0.254		10		
L	14.20	16.10	0.559	0.634		
L1	3.71	4.29	0.146	0.169		
ØР	3.56	3.66	0.14	0.144		
Ø P1	-	7.39	-	0.291		
Q	5.31	5.69	0.209	0.224		
R	4.52	5.49	0.178	0.216		
S	5.51 BSC		0.217	BSC		
	-	_	-			

#### **Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension Q



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